

# IRG4IBC30WPbF

## INSULATED GATE BIPOLAR TRANSISTOR

### Features

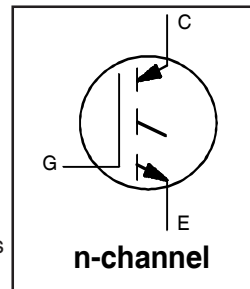
- Designed expressly for Switch-Mode Power Supply and PFC (power factor correction) applications
- 2.5kV, 60s insulation voltage ©
- Industry-benchmark switching losses improve efficiency of all power supply topologies
- 50% reduction of Eoff parameter
- Low IGBT conduction losses
- Latest-generation IGBT design and construction offers tighter parameters distribution, exceptional reliability
- Industry standard Isolated TO-220 Fullpak™ outline
- Lead-Free

### Benefits

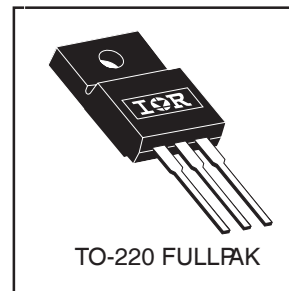
- Lower switching losses allow more cost-effective operation than power MOSFETs up to 150 kHz ("hard switched" mode)
- Of particular benefit to single-ended converters and boost PFC topologies 150W and higher
- Low conduction losses and minimal minority-carrier recombination make these an excellent option for resonant mode switching as well (up to >>300 kHz)

### Absolute Maximum Ratings

	Parameter	Max.	Units
$V_{CES}$	Collector-to-Emitter Breakdown Voltage	600	V
$I_C @ T_C = 25^\circ\text{C}$	Continuous Collector Current	17	A
$I_C @ T_C = 100^\circ\text{C}$	Continuous Collector Current	8.4	
$I_{CM}$	Pulsed Collector Current ①	92	
$I_{LM}$	Clamped Inductive Load Current ②	92	
$V_{GE}$	Gate-to-Emitter Voltage	$\pm 20$	V
$E_{ARV}$	Reverse Voltage Avalanche Energy ③	180	mJ
$P_D @ T_C = 25^\circ\text{C}$	Maximum Power Dissipation	45	W
$P_D @ T_C = 100^\circ\text{C}$	Maximum Power Dissipation	18	
$T_J$	Operating Junction and	-55 to + 150	°C
$T_{STG}$	Storage Temperature Range		
	Soldering Temperature, for 10 seconds	300 (0.063 in. (1.6mm from case )	
	Mounting torque, 6-32 or M3 screw.	10 lbf•in (1.1N•m)	



$V_{CES} = 600\text{V}$
$V_{CE(on) \text{ typ.}} = 2.1\text{V}$
@ $V_{GE} = 15\text{V}, I_C = 12\text{A}$



### Thermal Resistance

	Parameter	Typ.	Max.	Units
$R_{\theta JC}$	Junction-to-Case - IGBT	—	2.8	°C/W
$R_{\theta JA}$	Junction-to-Ambient, typical socket mount	—	65	
$W_t$	Weight	2.0 (0.07)	—	g (oz)

## Electrical Characteristics @ $T_J = 25^\circ\text{C}$ (unless otherwise specified)

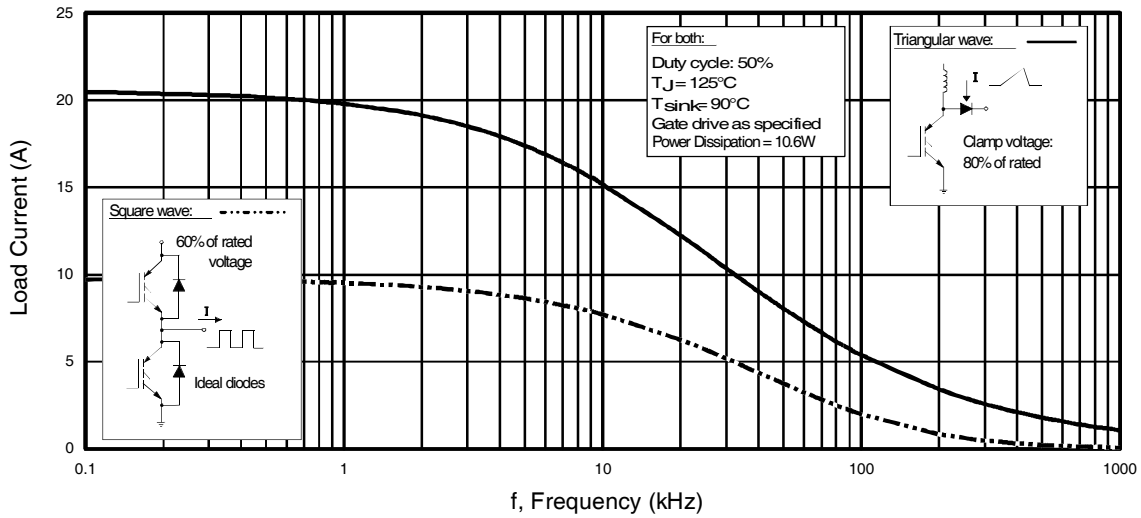
	Parameter	Min.	Typ.	Max.	Units	Conditions
$V_{(BR)CES}$	Collector-to-Emitter Breakdown Voltage	600	—	—	V	$V_{GE} = 0V, I_C = 250\mu A$
$V_{(BR)ECS}$	Emitter-to-Collector Breakdown Voltage ④	18	—	—	V	$V_{GE} = 0V, I_C = 1.0A$
$\Delta V_{(BR)CES}/\Delta T_J$	Temperature Coeff. of Breakdown Voltage	—	0.34	—	V/°C	$V_{GE} = 0V, I_C = 1.0mA$
$V_{CE(ON)}$	Collector-to-Emitter Saturation Voltage	—	2.1	2.7	V	$I_C = 12A$ $I_C = 23A$ $I_C = 12A, T_J = 150^\circ\text{C}$ $V_{GE} = 15V$ See Fig.2, 5
		—	2.45	—		
		—	1.95	—		
$V_{GE(th)}$	Gate Threshold Voltage	3.0	—	6.0		$V_{CE} = V_{GE}, I_C = 250\mu A$
$\Delta V_{GE(th)}/\Delta T_J$	Temperature Coeff. of Threshold Voltage	—	-11	—	mV/°C	$V_{CE} = V_{GE}, I_C = 250\mu A$
$g_{fe}$	Forward Transconductance ⑤	11	16	—	S	$V_{CE} = 100V, I_C = 12A$
$I_{CES}$	Zero Gate Voltage Collector Current	—	—	250	$\mu A$	$V_{GE} = 0V, V_{CE} = 600V$
		—	—	2.0		$V_{GE} = 0V, V_{CE} = 10V, T_J = 25^\circ\text{C}$
		—	—	1000		$V_{GE} = 0V, V_{CE} = 600V, T_J = 150^\circ\text{C}$
$I_{GES}$	Gate-to-Emitter Leakage Current	—	—	$\pm 100$	nA	$V_{GE} = \pm 20V$

## Switching Characteristics @ $T_J = 25^\circ\text{C}$ (unless otherwise specified)

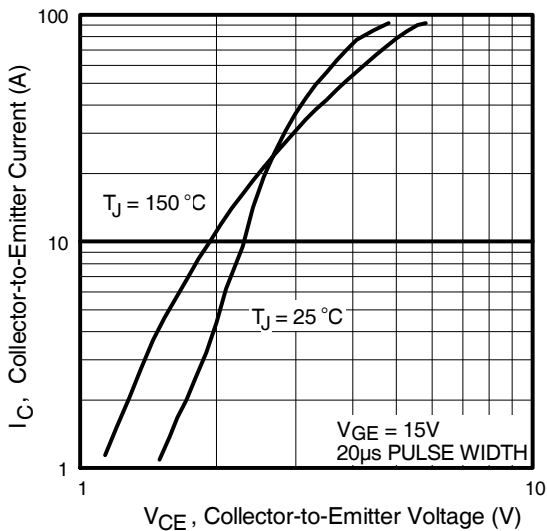
	Parameter	Min.	Typ.	Max.	Units	Conditions
$Q_g$	Total Gate Charge (turn-on)	—	51	76	nC	$I_C = 12A$ $V_{CC} = 400V$ $V_{GE} = 15V$ See Fig.8
$Q_{ge}$	Gate - Emitter Charge (turn-on)	—	7.6	11		
$Q_{gc}$	Gate - Collector Charge (turn-on)	—	18	27		
$t_{d(on)}$	Turn-On Delay Time	—	25	—	ns	$T_J = 25^\circ\text{C}$ $I_C = 12A, V_{CC} = 480V$ $V_{GE} = 15V, R_G = 23\Omega$ Energy losses include "tail" See Fig. 9, 10, 13, 14
$t_r$	Rise Time	—	16	—		
$t_{d(off)}$	Turn-Off Delay Time	—	99	150		
$t_f$	Fall Time	—	67	100		
$E_{on}$	Turn-On Switching Loss	—	0.13	—	mJ	See Fig. 9, 10, 13, 14
$E_{off}$	Turn-Off Switching Loss	—	0.13	—		
$E_{ts}$	Total Switching Loss	—	0.26	0.35		
$t_{d(on)}$	Turn-On Delay Time	—	24	—	ns	$T_J = 150^\circ\text{C}$ , $I_C = 12A, V_{CC} = 480V$ $V_{GE} = 15V, R_G = 23\Omega$ Energy losses include "tail" See Fig. 11,13, 14
$t_r$	Rise Time	—	17	—		
$t_{d(off)}$	Turn-Off Delay Time	—	150	—		
$t_f$	Fall Time	—	150	—		
$E_{ts}$	Total Switching Loss	—	0.55	—	mJ	
$L_E$	Internal Emitter Inductance	—	7.5	—	nH	Measured 5mm from package
$C_{ies}$	Input Capacitance	—	980	—	pF	$V_{GE} = 0V$ $V_{CC} = 30V$ $f = 1.0MHz$ See Fig. 7
$C_{oes}$	Output Capacitance	—	71	—		
$C_{res}$	Reverse Transfer Capacitance	—	18	—		

### Notes:

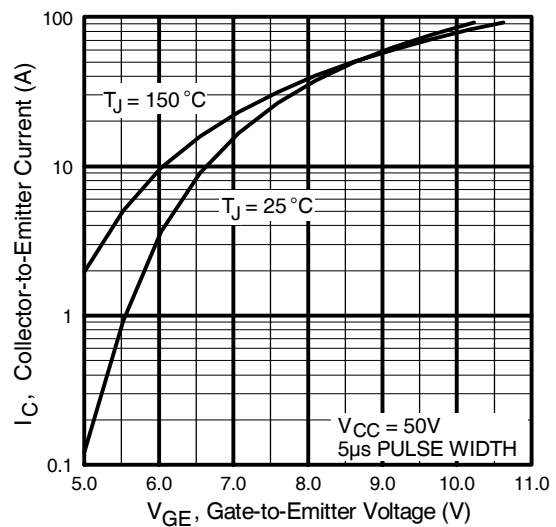
- ① Repetitive rating;  $V_{GE} = 20V$ , pulse width limited by max. junction temperature. ( See fig. 13b )
- ②  $V_{CC} = 80\%(V_{CES}), V_{GE} = 20V, L = 10\mu H, R_G = 23\Omega$ , (See fig. 13a)
- ③ Repetitive rating; pulse width limited by maximum junction temperature.
- ④ Pulse width  $\leq 80\mu s$ ; duty factor  $\leq 0.1\%$ .
- ⑤ Pulse width  $5.0\mu s$ , single shot.
- ⑥  $t = 60s, f = 60Hz$



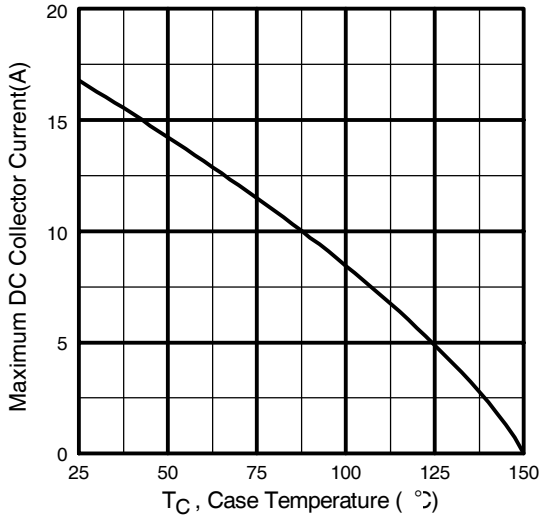
**Fig. 1 - Typical Load Current vs. Frequency**  
(For square wave,  $I = I_{\text{RMS}}$  of fundamental; for triangular wave,  $I = I_{\text{PK}}$ )



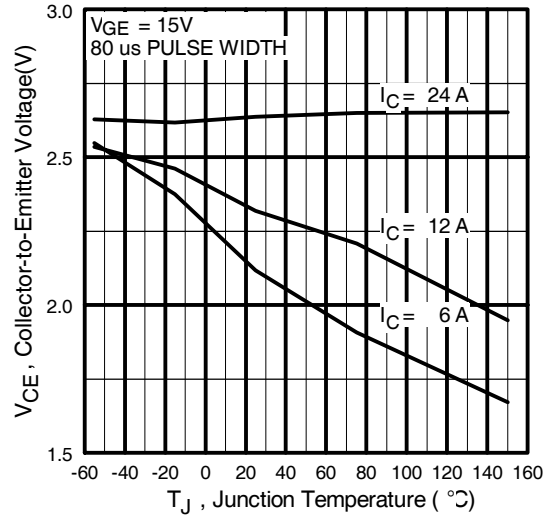
**Fig. 2 - Typical Output Characteristics**



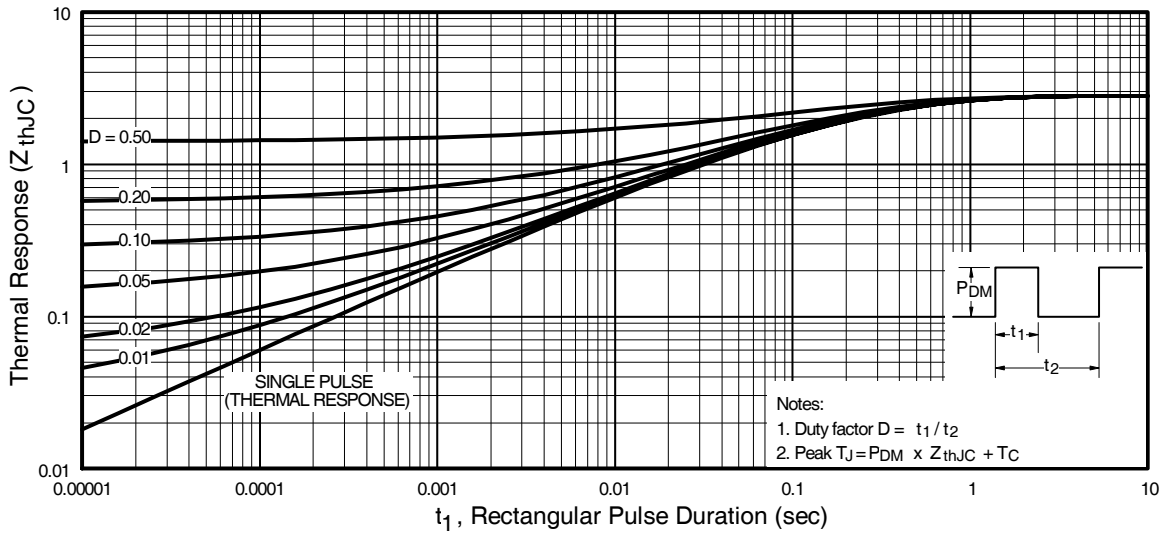
**Fig. 3 - Typical Transfer Characteristics**



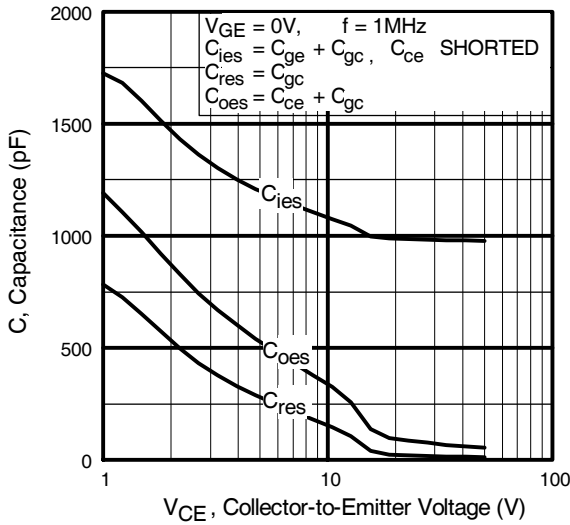
**Fig. 4** - Maximum Collector Current vs. Case Temperature



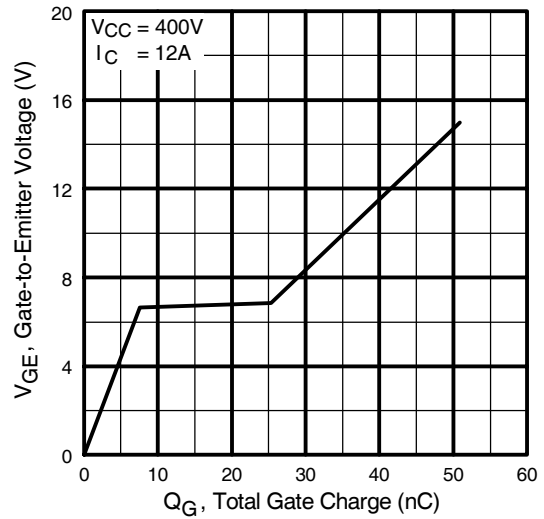
**Fig. 5** - Collector-to-Emitter Voltage vs. Junction Temperature



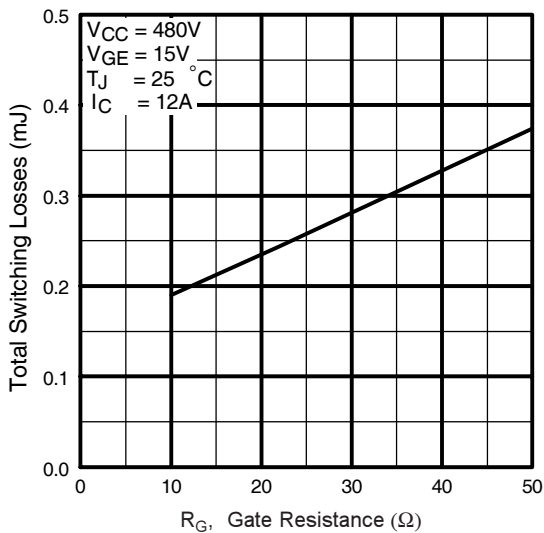
**Fig. 6** - Maximum Effective Transient Thermal Impedance, Junction-to-Case



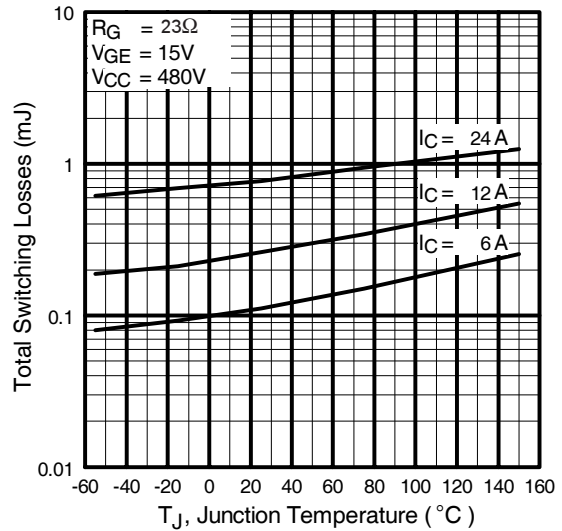
**Fig. 7** - Typical Capacitance vs. Collector-to-Emitter Voltage



**Fig. 8** - Typical Gate Charge vs. Gate-to-Emitter Voltage

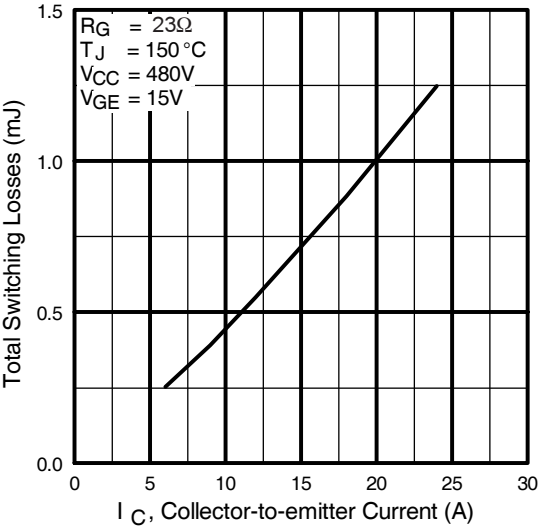


**Fig. 9** - Typical Switching Losses vs. Gate Resistance

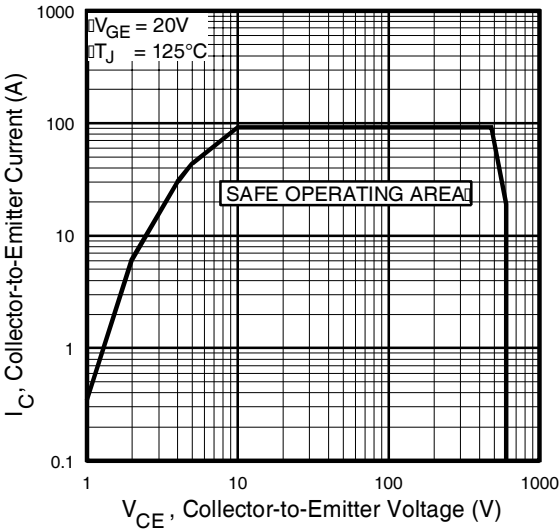


**Fig. 10** - Typical Switching Losses vs. Junction Temperature

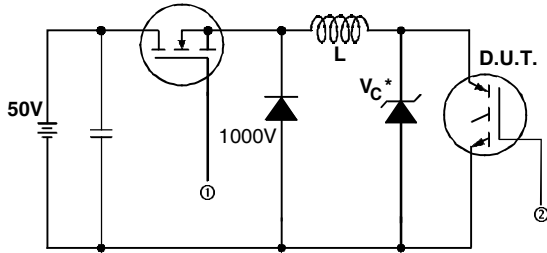
# IRG4IBC30WPbF



**Fig. 11** - Typical Switching Losses vs. Collector-to-Emitter Current

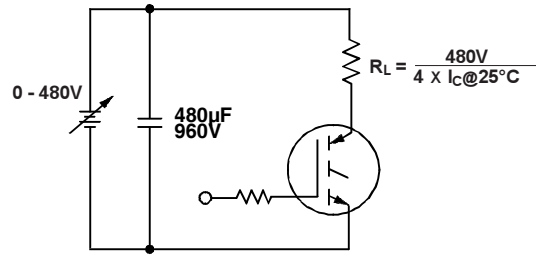


**Fig. 12** - Turn-Off SOA

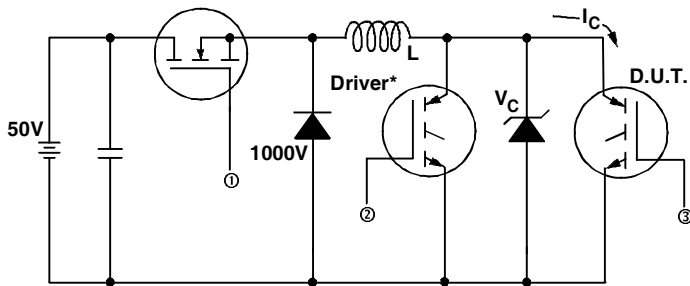


\* Driver same type as D.U.T.;  $V_c = 80\%$  of  $V_{ce(max)}$   
 \* Note: Due to the 50V power supply, pulse width and inductor will increase to obtain rated  $I_d$ .

**Fig. 13a** - Clamped Inductive Load Test Circuit

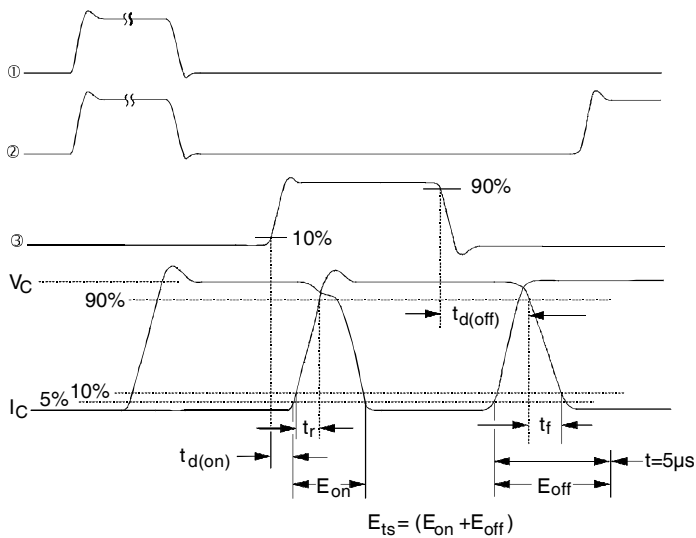


**Fig. 13b** - Pulsed Collector Current Test Circuit



**Fig. 14a** - Switching Loss Test Circuit

\* Driver same type as D.U.T.,  $V_C = 480V$



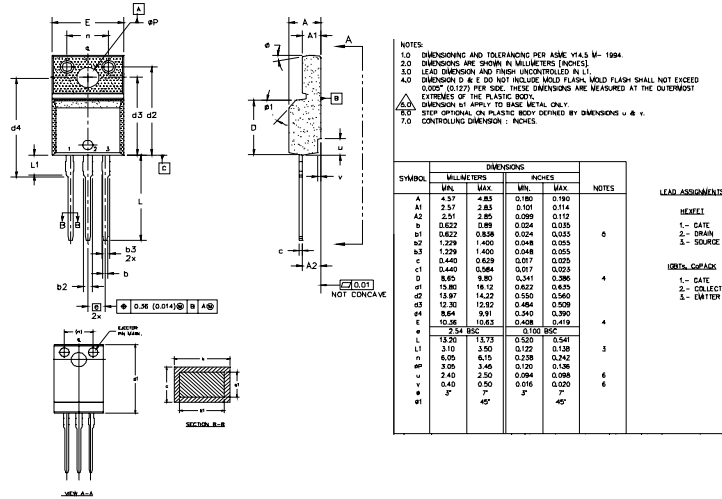
**Fig. 14b** - Switching Loss Waveforms

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## TO-220 Full-Pak Package Outline

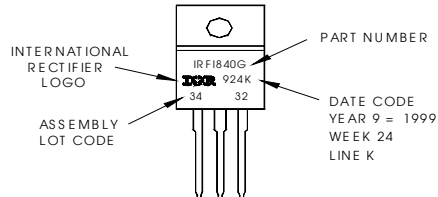
Dimensions are shown in millimeters (inches)



## TO-220 Full-Pak Part Marking Information

EXAMPLE: THIS IS AN IRF1840G  
WITH ASSEMBLY  
LOT CODE 3432  
ASSEMBLED ON WW 24 1999  
IN THE ASSEMBLY LINE "K"

**Note:** "P" in assembly line position indicates "Lead-Free"



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Data and specifications subject to change without notice. 06/04





Note: For the most current drawings please refer to the IR website at:  
<http://www.irf.com/package/>

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Сотрудничество с глобальными дистрибьюторами электронных компонентов, предоставляет возможность заказывать и получать с международных складов практически любой перечень компонентов в оптимальные для Вас сроки.

На всех этапах разработки и производства наши партнеры могут получить квалифицированную поддержку опытных инженеров.

Система менеджмента качества компании отвечает требованиям в соответствии с ГОСТ Р ИСО 9001, ГОСТ РВ 0015-002 и ЭС РД 009

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